

**PLEASE AMEND THE SPECIFICATION AS FOLLOWS:**

After the title, insert -- This is a continuation of Patent Application serial number 09/557,395, filing date 4/24/00, Method For Integrating Low-K Materials In Semiconductor Fabrication, assigned to the same assignee as the present invention.

**REMARKS**

A reference to the parent case has been added by Preliminary Amendment to this Continuation Patent Application.

The application is believed to be in condition for allowance. Allowance of the subject Patent Application is therefore respectfully requested.

Respectfully submitted,



STEPHEN B. ACKERMAN, REG. NO. 37,761

## **REMARKS**

### **In the Specification**

A reference to the parent case has been added by Preliminary Amendment to this Continuation. The grammatical error “--a low-K layers--“ has been corrected to read “--low-K layers--”

### **In the Claims**

New claims are submitted with this Continuation. These claims describe a Dual Damascene structure and a Single Damascene structure that are the results of the claimed methods of the parent application.

The application is believed to be in condition for allowance. Allowance of the subject Patent application is therefore respectfully requested.

Respectfully submitted,



STEPHEN B. ACKERMAN, REG. NO. 37,761

## **MARKED UP VERSION**

In the paragraph entitled "Field of the Invention" please make the grammatical correction as shown.

### **1) Field of the Invention**

This invention relates generally to fabrication of a semiconductor device and more particularly to a method for forming [a] low-K dielectric layers with improved thermal stability and structural strength by forming pillars, comprising material with good thermal stability and structural strength within the low-K dielectric layer.